

Rev. H Oct.-2018

WR0553 肖特基二极管

Schottky Barrier Diode in a TO-220 Plastic Package.

低损耗 高效率

Low power loss, high efficiency.

适用于低电压、高频逆变器、自由轮、极性保护应用。

For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.

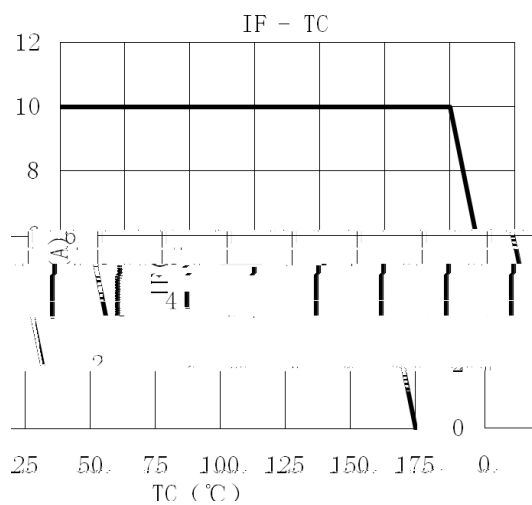
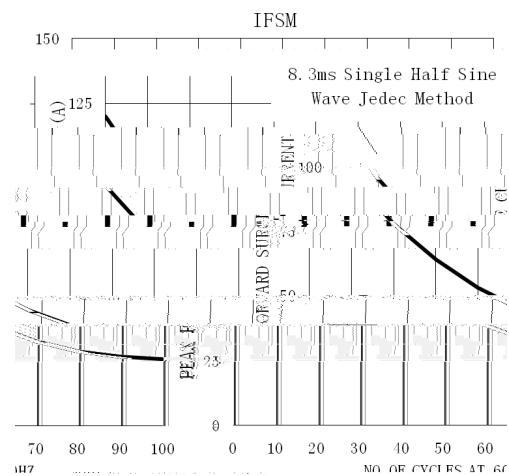
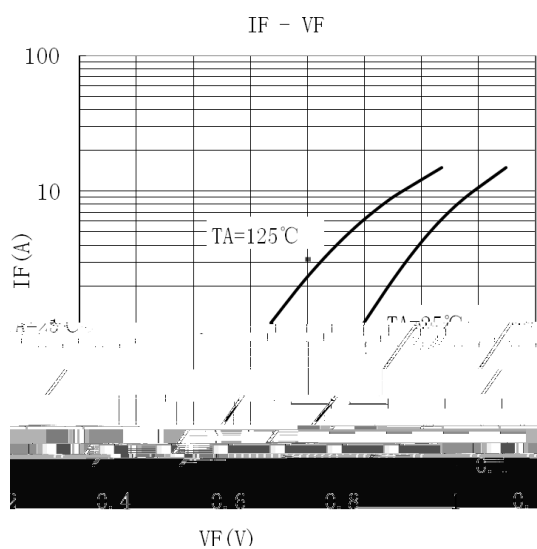
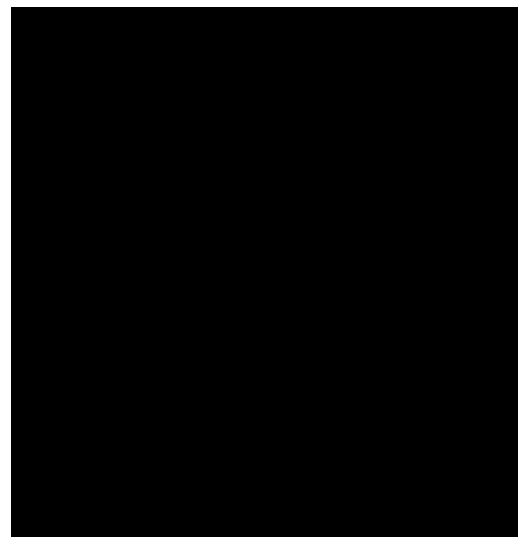
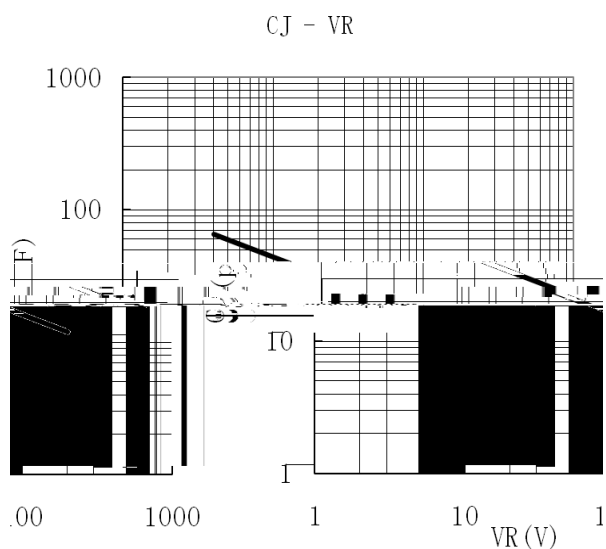


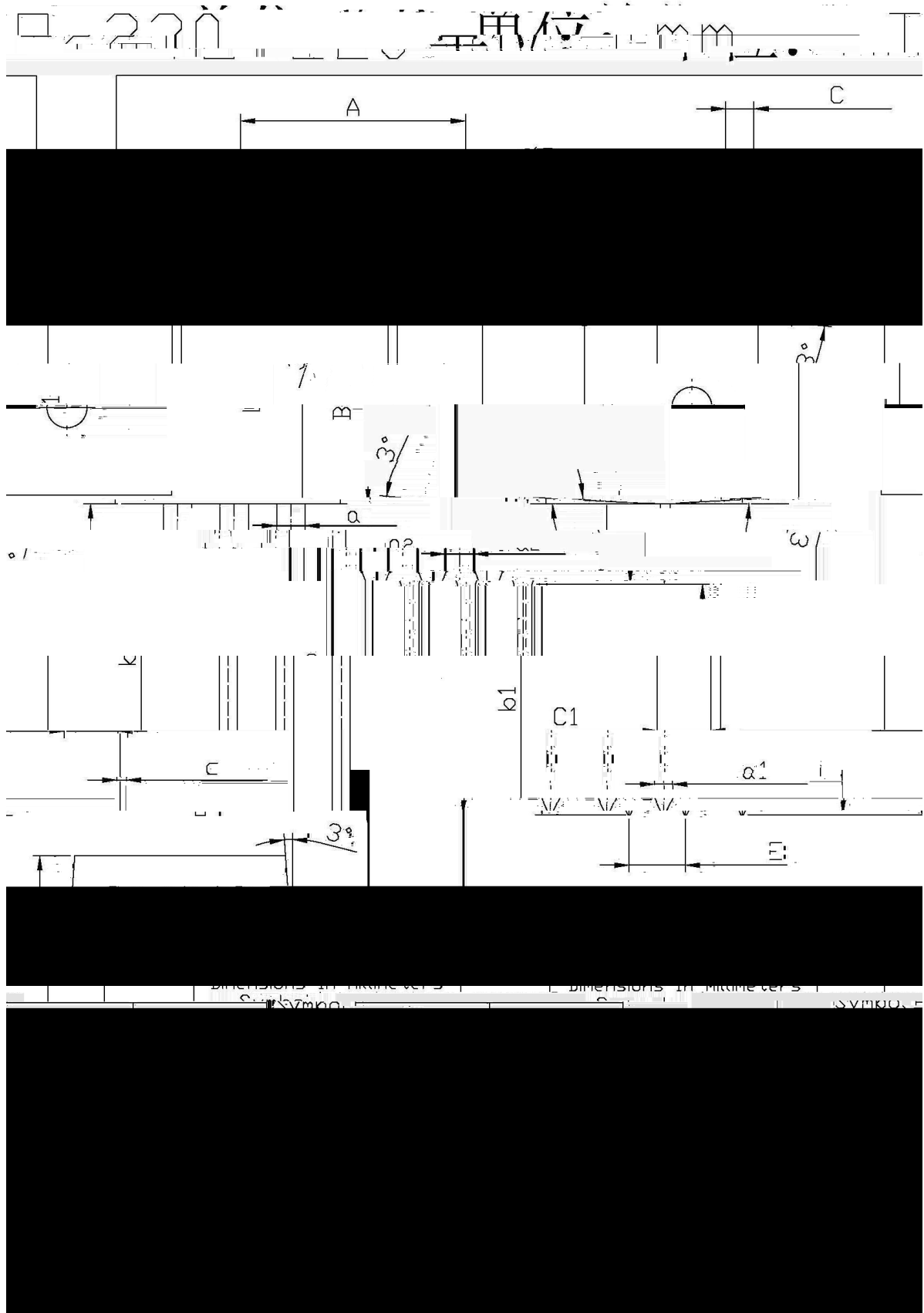
PIN1 Anode PIN 2 Cathode PIN 3 Anode

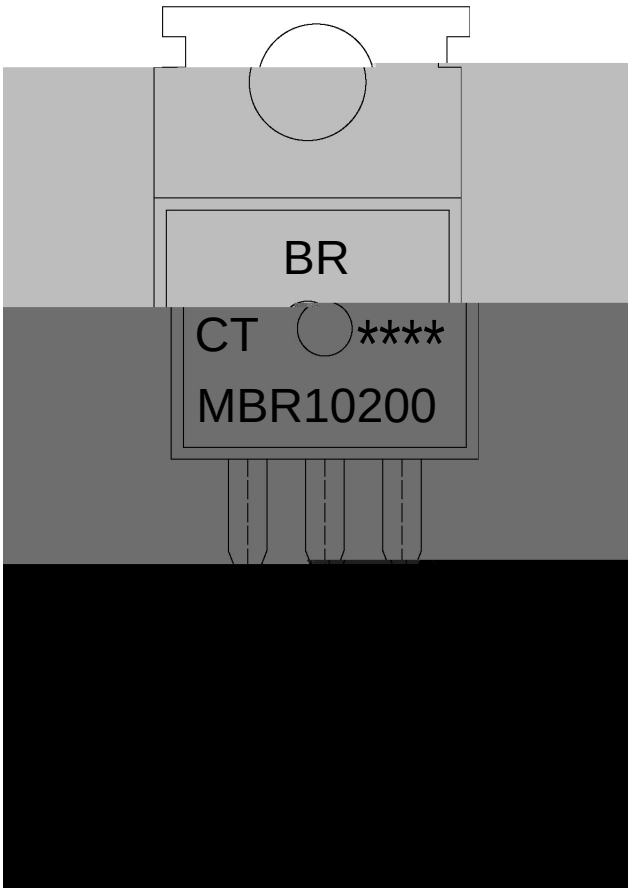
请参见“标记说明”。

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
Peak Repetitive Forward Current	$I_{F(AV)}$	10	A
Average Rectified Forward Current	I_{FRM}	10	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	150	A
Repetitive Peak Reverse Surge Current	I_{RRM}	0.5	A
Thermal Resistance Junction to Case	R_{JC}	2.5	/W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Current Voltage	V_R		200			V
Forward Voltage	V_F	$I_F=5A$			0.99	V
		$I_F=5A(T_C=125^\circ C)$			0.87	V
Instantaneous Reverse Current	I_R	$V_R=200V$			0.15	mA
		$V_R=200V(T_C=125^\circ C)$			150	mA
Voltage Rate of Change	dv/dt				10000	V/ s







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EU χ	ಹ 3 " Γ
P EU43533 χ	ಹ F β 3 N
FW:	ಹ 1 γ Γ =
---- χ	ಹ 1 F ḡ N Γ 1 6 1 F ḡ N ψ ρ
Note:	
BR:	Company Code
MBR10200 χ	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.

